

# DSt Low Noise JFET Products



Low Noise JFETs					
Device No.	Input Cap. Ciss (pF) Vds=0V, Vgs=0V	Gm (mS) Vds=3V Vgs=0V	Noise, En nV /Root HZ Vds=3V, f=100kHz	Die size	Additional Information
SF291	8.0	45	0.65	900 x 900 $\mu$ m	Three terminal device for amplifiers requiring high transconductance and low noise.
SF201	1.6	10	1.3	900 x 900 $\mu$ m	Four terminal device with an integrated charge reset mechanism and feedback capacitance. Suitable for large area nuclear detectors coupled to charge sensitive amplifiers. For electron charge collection (negative biased detectors)
SF202	1.6	10	1.3	900 x 900 $\mu$ m	Four terminal device with an integrated charge reset mechanism and feedback capacitance. Suitable for large area nuclear detectors coupled to charge sensitive amplifiers. For hole charge collection (positive biased detectors).
SF203	1.6	10	1.3	900 x 900 $\mu$ m	Suitable for positive or negative charge collection. Charge reset mechanism disabled.
SF181	0.8	5	1.8	900 x 900 $\mu$ m	Four terminal device with an integrated charge reset mechanism and feedback capacitance. Suitable for medium area nuclear detectors coupled to charge sensitive amplifiers. For electron charge collection (negative biased detectors).
SF51	0.4	2.3	2.2	900 x 900 $\mu$ m	Four terminal device with an integrated charge reset mechanism and feedback capacitance. Suitable for small area nuclear detectors coupled to charge sensitive amplifiers. For electron charge collection (negative biased detectors) .